## Abstract Submitted for the MAR05 Meeting of The American Physical Society

Spectroscopic ellipsometry study of optical anisotropy in Gd5Si2Ge2 and comparison with reflectance difference spectra S.J. LEE, Materials and Engineering Physics Program, Ames Lab, J.M. PARK, Department of Physics and Astronomy, J.E. SNYDER, D.C. JILES, T.A. LOGRASSO, D.L. SCHLAGEL, A.O. PECHARSKY, Materials and Engineering Physics Program, Ames Lab, D.W. LYNCH, Department of Physics and Astronomy, ISU, Ames, IA  $50011 - \text{Recently}, \text{Gd}_5\text{Si}_2\text{Ge}_2$  has been extensively studied due to its giant magnetocaloric effect, colossal magnetostriction, and giant magnetoresistance in the region of an unusual first-order magnetic-structural phase transformation. In this presentation, we report the complex dielectric functions of single crystals of  $Gd_5Si_2Ge_2$ obtained using spectroscopic ellipsometry (SE) in the photon energy range 1.5 to 5.0 eV. Reflectance difference (RD) spectra for  $Gd_5Si_2Ge_2$  single crystals have been measured by reflectance difference spectroscopy (RDS). Reflectance difference spectra for the a-b and b-c planes of single crystals of  $Gd_5Si_2Ge_2$  were derived from the complex dielectric functions obtained from SE measurements and compared with those obtained from RDS measurements at near normal incidence. The measured spectra agreed well. The in-plane optical anisotropy of the sample is mainly due to intrinsic bulk properties because it has large values  $(4 \times 10^{-2})$  compared to surface induced optical anisotropies, with values of only of about  $10^{-3}$  for a typical cubic material.

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